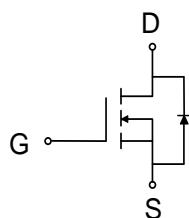
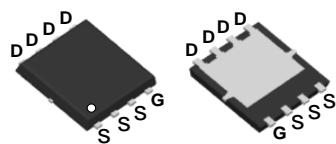


## N-Channel Advanced Trench MOSFET

**MSR3R1N03SD**

**PDFN5x6**



$V_{DS}$	30	V
$R_{DS(on),Typ}@ V_{GS}=10\text{ V}$	2.1	mΩ
$I_D$	120	A

### Features

- 1、Low on – resistance
- 2、High power package (PDFN5X6)
- 3、Halogen free

### Applications

- 1、Power Management Switches
- 2、PWM Application
- 3、Load Switch

**Maximum ratings, at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	30	V
$V_{GS}$	Gate-Source voltage	$\pm 20$	V
$I_D$	Continuous drain current ③	$T_C=25^\circ\text{C}$	A
		$T_C=100^\circ\text{C}$	A
$I_{DM}$	Pulse drain current tested ①	$T_C=25^\circ\text{C}$	A
EAS	Avalanche energy, single pulsed ②	342	mJ
PD	Maximum power dissipation	$T_C=25^\circ\text{C}$	W
$T_{STG}, T_J$	Storage and Junction Temperature Range	-55 to 150	°C

## Thermal Characteristics

Symbol	Parameter	Rating	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	1.83	°C/W

## Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
--------	-----------	-----------	------	------	------	------

Static Electrical Characteristics @T<sub>j</sub>=25°C (unless otherwise stated)

V(BR)DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	--	--	1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2.2	V
R <sub>D(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	--	2.1	3.1	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	--	3.7	5.5	mΩ

## Dynamic Electrical Characteristics@T<sub>j</sub> = 25°C (unless otherwise stated)

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V , f=1MHz	--	3833	--	pF
C <sub>oss</sub>	Output Capacitance		--	437	--	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	350	--	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =30A , V <sub>GS</sub> =10V	--	72	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	46	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	13	--	nC

## Switching Characteristics

Td(on)	Turn-on Delay Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V I <sub>D</sub> =30A, R <sub>G</sub> =3Ω,	--	14	--	ns
Tr	Turn-on Rise Time		--	18	--	ns
Td(off)	Turn-Off Delay Time		--	40	--	ns
Tf	Turn-Off Fall Time		--	12	--	ns

## Source- Drain Diode Characteristics@ T<sub>j</sub> = 25°C (unless otherwise stated)

V <sub>SD</sub>	Forward on voltage	I <sub>S</sub> =30A,V <sub>GS</sub> =0V	--	--	1.2	V
I <sub>S</sub>	Body Diode Forward Current	--	--	--	120	A
I <sub>SM</sub>	Max Pulsed Drain-source diode forward current		--	--	360	A

NOTE: ① Repetitive Rating: Pulse width limited by maximum junction temperature.

② EAS Condition: L=0.5mH, V<sub>DD</sub>=30V, V<sub>G</sub>=10V Start T<sub>J</sub>=25°C, I<sub>AS</sub>=25A

③ Pulse test: Width≤300us, Duty Cycle≤0.5%

## Typical Characteristics

### N- Channel Typical Characteristics

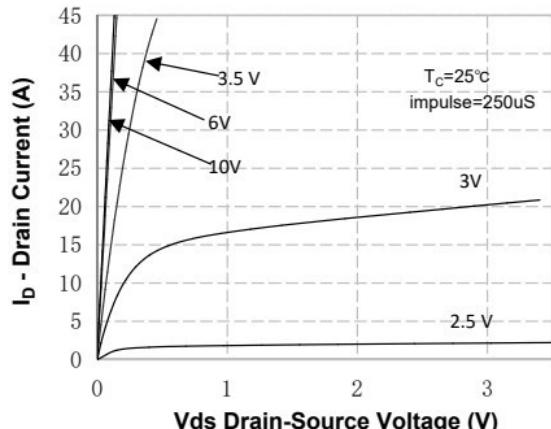


Figure 1. On-Region Characteristics

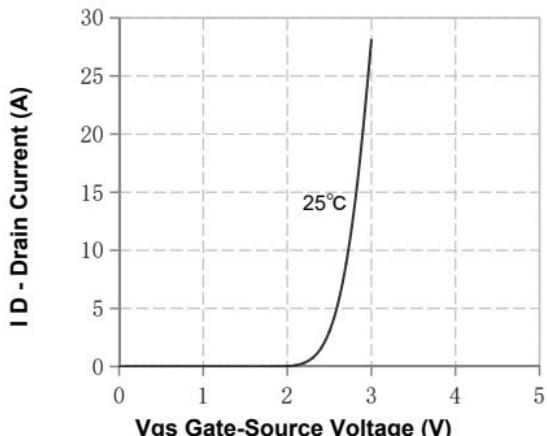


Figure 2. Transfer Characteristics

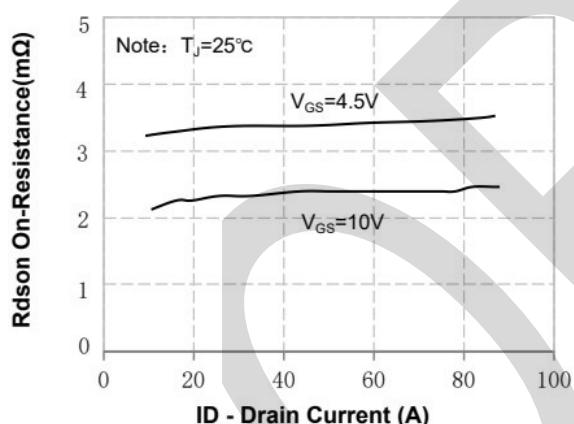


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

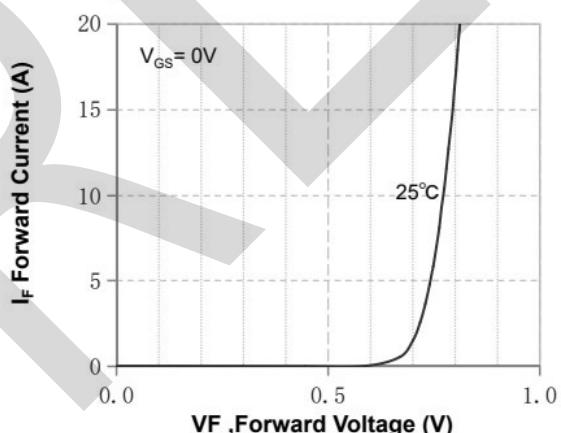


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

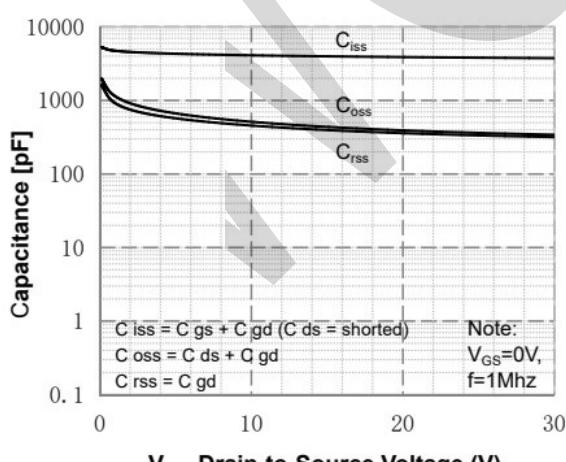


Figure 5. Capacitance Characteristics

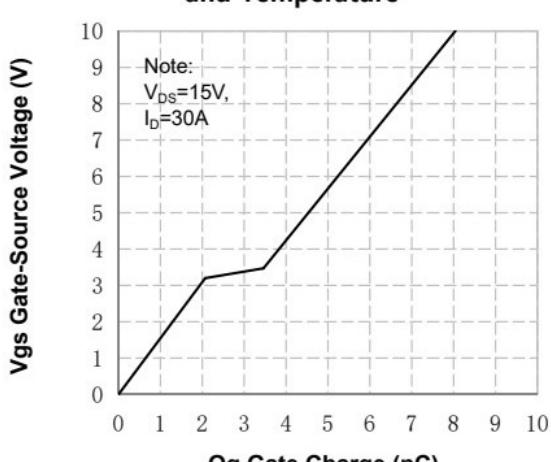
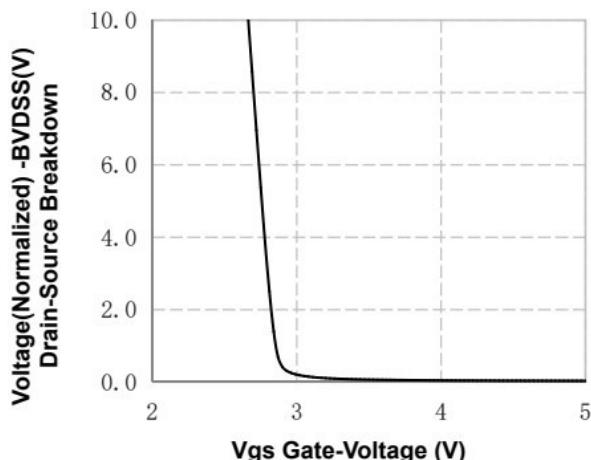


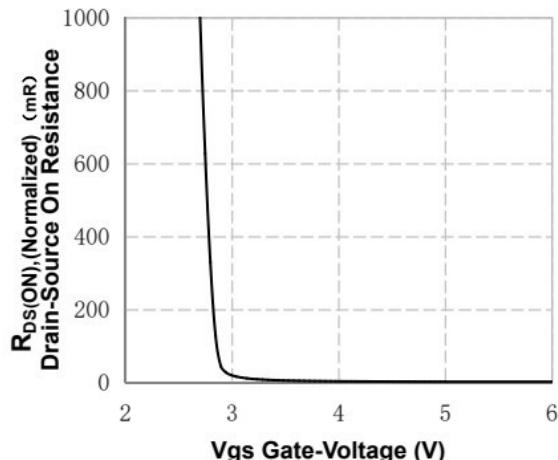
Figure 6. Gate Charge Characteristics

## Typical Characteristics

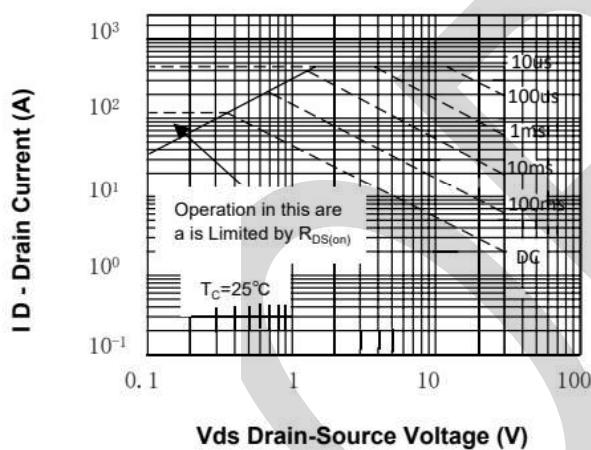
### N- Channel Typical Characteristics (Continued)



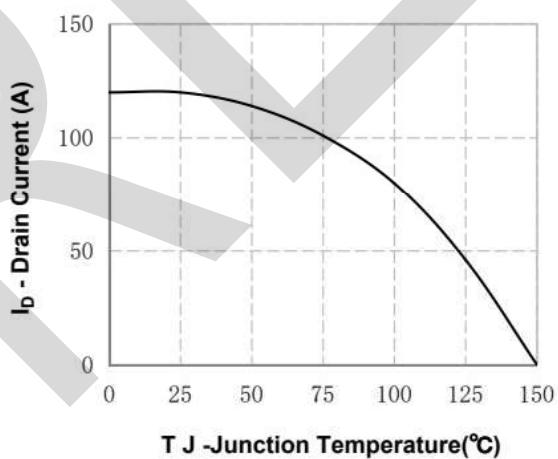
**Figure 7. Breakdown Voltage Variation vs Gate-Voltage**



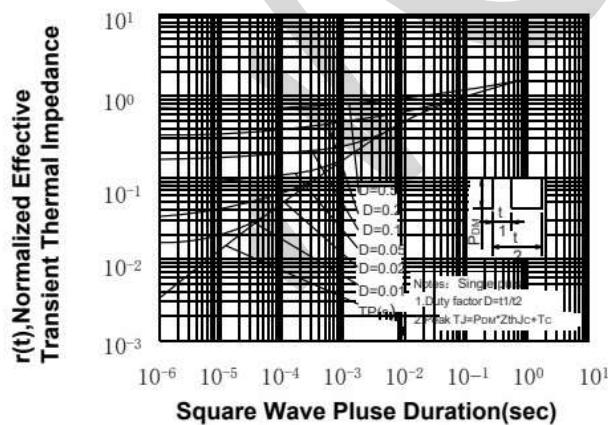
**Figure 8. On-Resistance Variation vs Gate Voltage**



**Figure 9. Maximum Safe Operating Area**

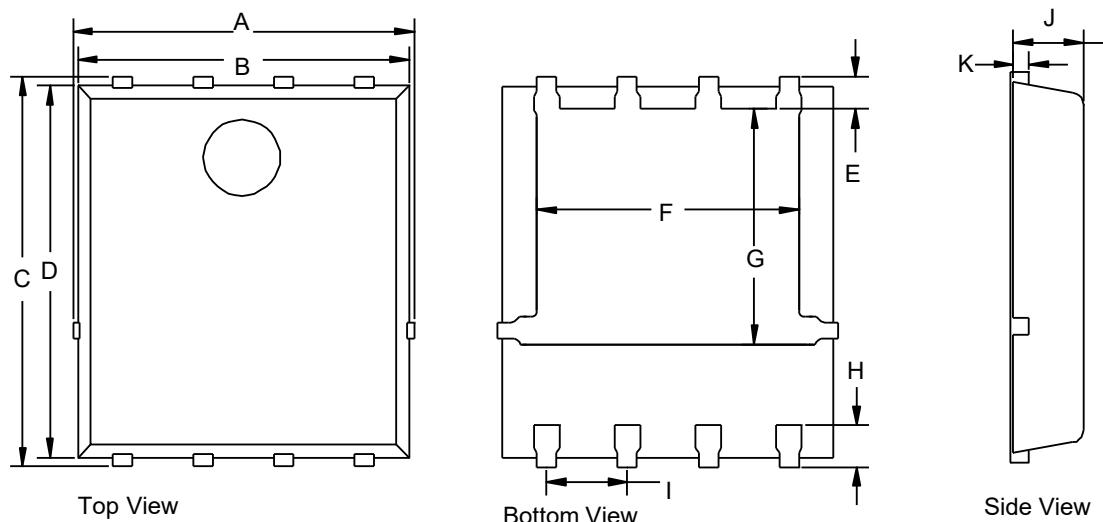


**Figure 10. Maximum Continuous Drain Current vs Case Temperature**



**Figure 11. Transient Thermal Response Curve**

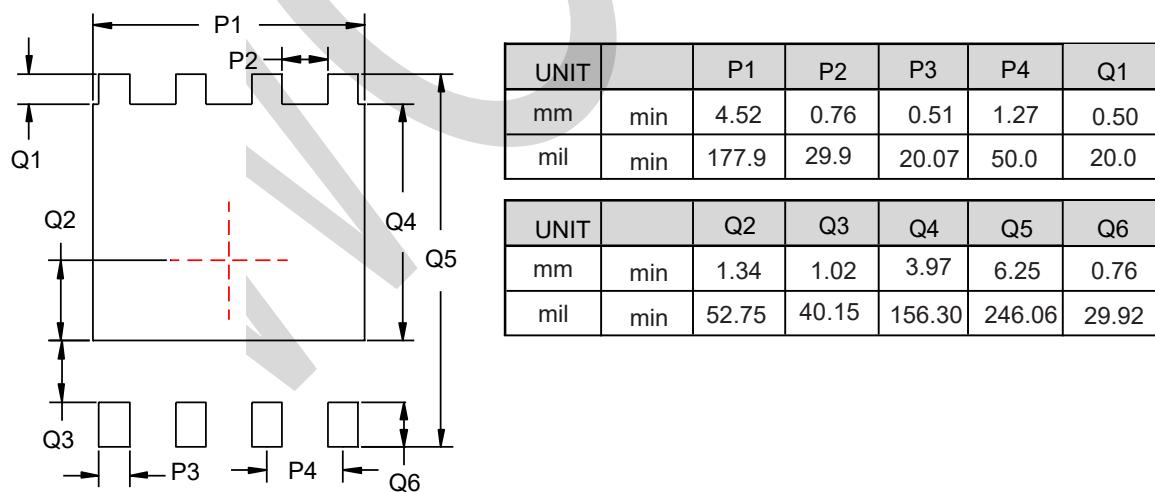
## PACKAGE OUTLINE DIMENSIONS



## PDFN5x6 mechanical data

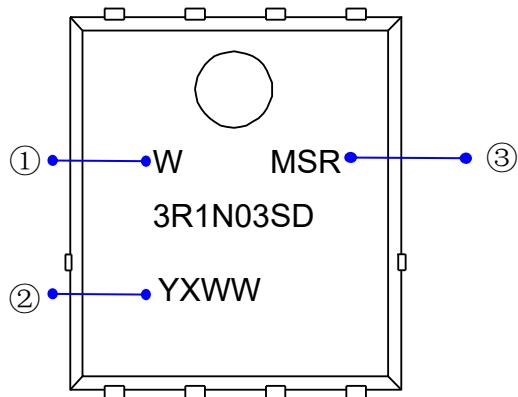
UNIT		A	B	C	D	E	F	G	H	I	J	K
mm	min	4.90	4.8	5.90	5.66	0.60	3.90	3.30	0.53	1.27	0.9	0.254
	max	5.55	5.4	6.35	6.06		4.32	3.92	0.76		1.2	
mil	min	192.9	188.9	232.3	222.8	23.6	153.5	129.9	20.8	50.0	35.4	10.0
	max	218.5	212.6	250.0	238.6		170.1	154.3	29.9		47.2	

## PDFN5x6 Suggested Pad Layout



## PACKAGE OUTLINE DIMENSIONS

### Marking Information



- ① W : Company's trademark
- ② Product model : MSR3R1N03SD
- ③ PDC information:

Y X WW

WW:Week code(01 to 53)  
X:Internal identification code  
Y:Year code(ex:0=2020)

DRV